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Low temperature H⁺ irradiation and in situ DLTS measurements on ZnO

Semiconductor materials have been irradiated with 1.6 MeV protons at a temperature of 25 K after which in situ electrical characterization was performed to study the electrical active defects created during the irradiation. High resolution Laplace-DLTS was used to determine activation energies, capture cross-sections, defect concentrations and defect annealing kinetics.

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